# 2SD2259

## Silicon NPN epitaxial planar type

### For low-frequency amplification

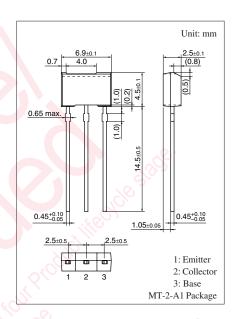
#### ■ Features

- High forward current transfer ratio h<sub>FE</sub>
- ullet Low collector-emitter saturation voltage  $V_{\text{CE(sat)}}$
- Allowing supply with the radial taping

### ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Symbol Rating	
Collector-base voltage (Emitter open)	$V_{CBO}$	20	V
Collector-emitter voltage (Base open)	$V_{CEO}$	20	V
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	15	V
Collector current	$I_{C}$	0.7	A
Peak collector current	$I_{CP}$	1.5	A
Collector power dissipation *	P <sub>C</sub>	1	W
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°CO

Note) \*: Printed circuit board: Copper foil area of 1 cm<sup>2</sup> or more, and the board thickness of 1.7 mm for the collector portion

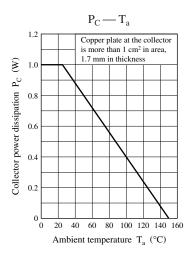


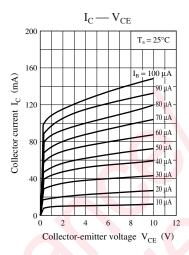
### ■ Electrical Characteristics $T_a = 25$ °C $\pm 3$ °C

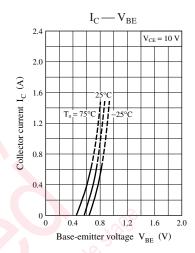
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = 10 \mu\text{A},  I_E = 0$	20	0.		V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = 1 \text{ mA}, I_B = 0$	20			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = 10 \mu\text{A}, I_C = 0$	15			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 15 \text{ V}, I_{E} = 0$			1	μΑ
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = 15 \text{ V}, I_{B} = 0$			10	μΑ
Forward current transfer ratio *	h <sub>FE</sub>	$V_{CE} = 10 \text{ V}, I_{C} = 150 \text{ mA}$	1 000		2500	_
Collector-emitter saturation voltage *	V <sub>CE(sat)</sub>	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.15	0.40	V
Transition frequency	$f_T$	$V_{CB} = 20 \text{ V}, I_E = -20 \text{ mA}, f = 200 \text{ MHz}$		55		MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$		10	15	pF
(Common base, input open circuited)						

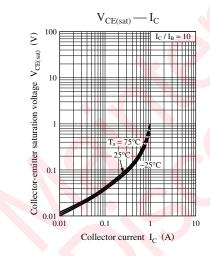
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

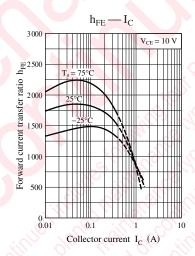
2. \*: Pulse measurement

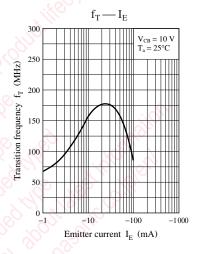


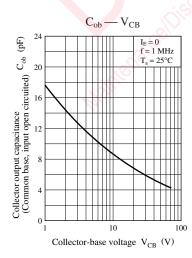












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